Inverting Schmitt trigger Rev. 04 — 17 July 2007

#### **General description** 1.

74HC1G14 and 74HCT1G14 are high-speed Si-gate CMOS devices. They provide an inverting buffer function with Schmitt trigger action. These devices are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC14 and 74HCT14.

#### **Features** 2.

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- Specified from –40 °C to +125 °C

#### **Applications** 3.

- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators

#### **Ordering information** 4.

Type number	Package							
	Temperature range	Name	Description	Version				
74HC1G14GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package;	SOT353-1				
74HCT1G14GW			5 leads; body width 1.25 mm					
74HC1G14GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74HCT1G14GV								

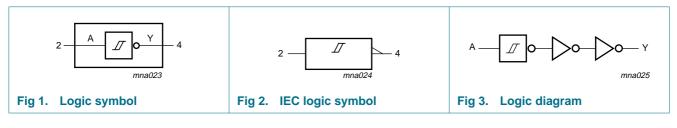


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## 5. Marking

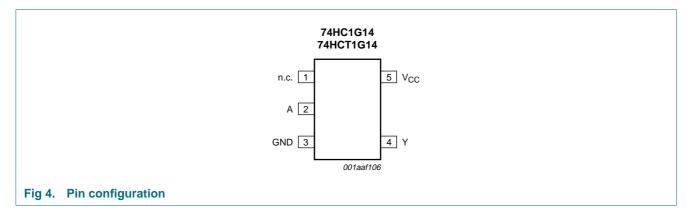
Table 2.   Marking codes	
Type number	Marking
74HC1G14GW	HF
74HCT1G14GW	TF
74HC1G14GV	H14
74HCT1G14GV	T14

# 6. Functional diagram



## 7. Pinning information

## 7.1 Pinning



## 7.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
n.c.	1	not connected
А	2	data input
GND	3	ground (0 V)
Y	5	data output
V <sub>CC</sub>	5	supply voltage

# 8. Functional description

### Table 4.Function table

*H* = *HIGH* voltage level; *L* = *LOW* voltage level

Input	Output
A	Y
L	Н
Н	L

## 9. Limiting values

### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{O}$ < -0.5 V or $V_{O}$ > $V_{CC}$ + 0.5 V	-	±20	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of  $\mathsf{P}_{tot}$  derates linearly with 2.5 mW/K.

## **10. Recommended operating conditions**

### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G14			74HCT1G14			Unit
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C

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# **11. Static characteristics**

### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	
For type	74HC1G14	·						
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	6.0	-	5.9	-	V
		$I_{O}$ = -2.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
		$I_{O}$ = -2.6 mA; $V_{CC}$ = 6.0 V	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 2.0 V	-	0	0.1	-	0.1	V
		$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 4.5 V	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O}$ = 2.6 mA; $V_{CC}$ = 6.0 V	-	0.16	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μΑ
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	pF
V <sub>T+</sub>	positive-going	see Figure 7 and 8						
	threshold voltage	$V_{CC} = 2.0 V$	0.7	1.09	1.5	0.7	1.5	V
		$V_{CC} = 4.5 V$	1.7	2.36	3.15	1.7	3.15	V
		$V_{CC} = 6.0 V$	2.1	3.12	4.2	2.1	4.2	V
V <sub>T-</sub>	negative-going	see Figure 7 and 8						
	threshold voltage	$V_{CC} = 2.0 V$	0.3	0.60	0.9	0.3	0.9	V
		$V_{CC} = 4.5 V$	0.9	1.53	2.0	0.9	2.0	V
		$V_{CC} = 6.0 V$	1.2	2.08	2.6	1.2	2.6	V
V <sub>H</sub>	hysteresis voltage	see Figure 7 and 8						
		$V_{CC} = 2.0 V$	0.2	0.48	1.0	0.2	1.0	V
		$V_{CC} = 4.5 V$	0.4	0.83	1.4	0.4	1.4	V
		$V_{CC} = 6.0 V$	0.6	1.04	1.6	0.6	1.6	V
For type	74HCT1G14							
V <sub>он</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = -20 \ \mu A; V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
lı	input leakage current	$V_{I}$ = $V_{CC}$ or GND; $V_{CC}$ = 5.5 V	-	-	1.0	-	1.0	μΑ

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Symbol	Parameter	Conditions	–40 °C to +85 °C			_40 °C t	–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μA
ΔI <sub>CC</sub>	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	500	-	850	μA
CI	input capacitance		-	1.5	-	-	-	pF
V <sub>T+</sub>	positive-going threshold voltage	see Figure 7 and 8						
		$V_{CC} = 4.5 V$	1.2	1.55	1.9	1.2	1.9	V
		$V_{CC} = 5.5 V$	1.4	1.80	2.1	1.4	2.1	V
V <sub>T-</sub>	negative-going	see Figure 7 and 8						
	threshold voltage	$V_{CC} = 4.5 V$	0.5	0.76	1.2	0.5	1.2	V
		$V_{CC} = 5.5 V$	0.6	0.90	1.4	0.6	1.4	V
V <sub>H</sub>	hysteresis voltage	see Figure 7 and 8						
		$V_{CC} = 4.5 V$	0.4	0.80	-	0.4	-	V
		V <sub>CC</sub> = 5.5 V	0.4	0.90	-	0.4	-	V

#### Table 7. Static characteristics ... continued

# 12. Dynamic characteristics

#### **Dynamic characteristics** Table 8.

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25 \circ C$ . For test circuit see Figure 6

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	–40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	]
For type	74HC1G14	'							
t <sub>pd</sub>	propagation delay	A to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	25	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	12	31	-	38	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	11	26	-	32	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[2]	-	20	-	-	-	pF
For type	74HCT1G14								
t <sub>pd</sub>	propagation delay	A to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	17	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	15	-	-	-	ns
C <sub>PD</sub>	power dissipation capacitance	$V_{I}$ = GND to $V_{CC}$ – 1.5 V	[2]	-	22	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $C_{PD}$  is used to determine the dynamic power dissipation P<sub>D</sub> ( $\mu$ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

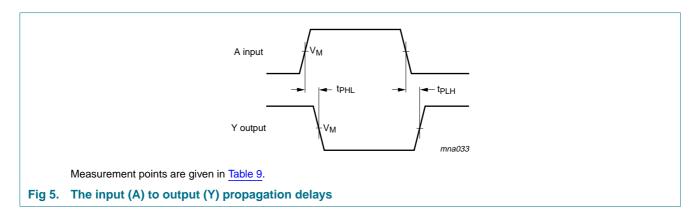
 $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz

 $C_L$  = output load capacitance in pF;  $V_{CC}$  = supply voltage in Volts

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs

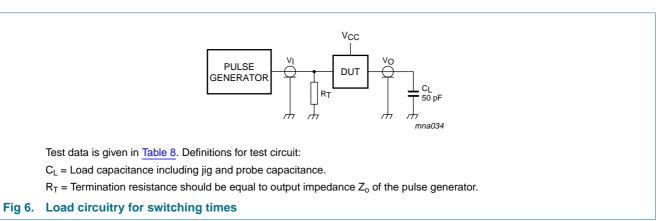
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# 13. Waveforms

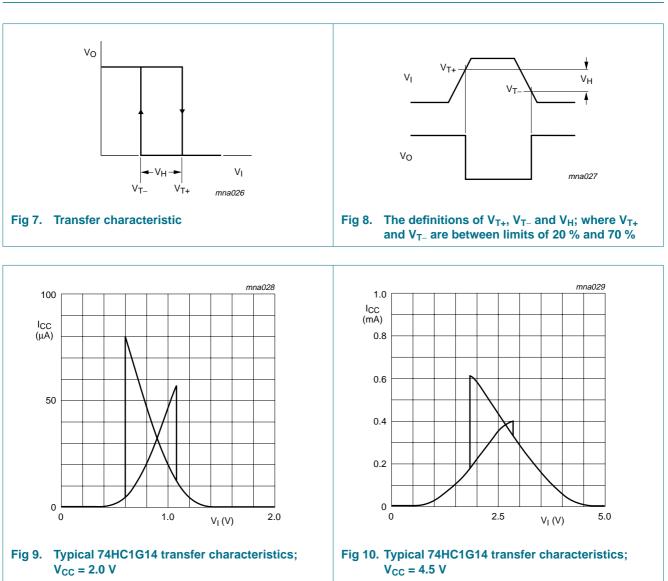


#### Table 9.Measurement points

Type number	number Input		Output
	VI	V <sub>M</sub>	V <sub>M</sub>
74HC1G14	GND to V <sub>CC</sub>	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT1G14	GND to 3.0 V	1.5 V	$0.5\times V_{CC}$



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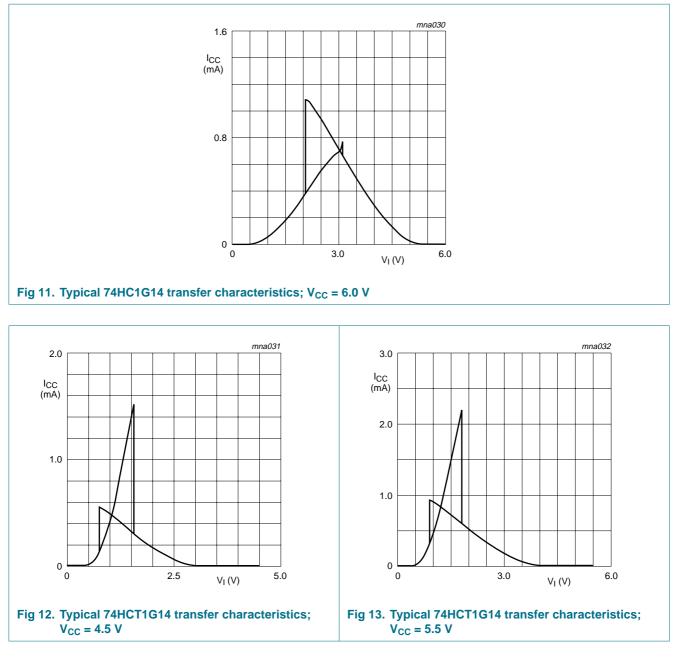


# 14. Transfer characteristics waveforms

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## **15. Application information**

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $\mathsf{P}_{\mathsf{add}} = \mathsf{f}_{\mathsf{i}} \times (\mathsf{t}_{\mathsf{r}} \times \Delta \mathsf{I}_{\mathsf{CC}(\mathsf{AV})} + \mathsf{t}_{\mathsf{f}} \times \Delta \mathsf{I}_{\mathsf{CC}(\mathsf{AV})}) \times \mathsf{V}_{\mathsf{CC}}$ 

Where:

 $P_{add}$  = additional power dissipation ( $\mu$ W)

 $f_i = input frequency (MHz)$ 

 $t_r$  = rise time (ns); 10 % to 90 %

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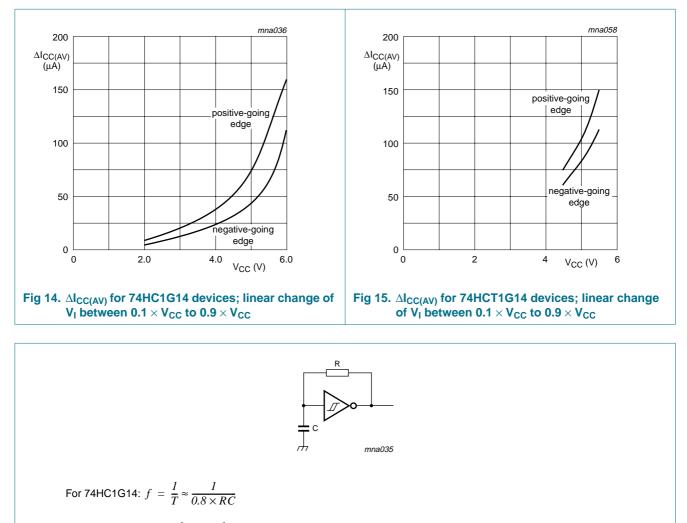
 $t_f$  = fall time (ns); 90 % to 10 %

 $\Delta I_{CC(AV)}$  = average additional supply current (µA)

 $\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in Figure 14 and 15.

74HC1G14 and 74HCT1G14 used in relaxation oscillator circuit, see Figure 16.

Remark: All values given are typical unless otherwise specified.

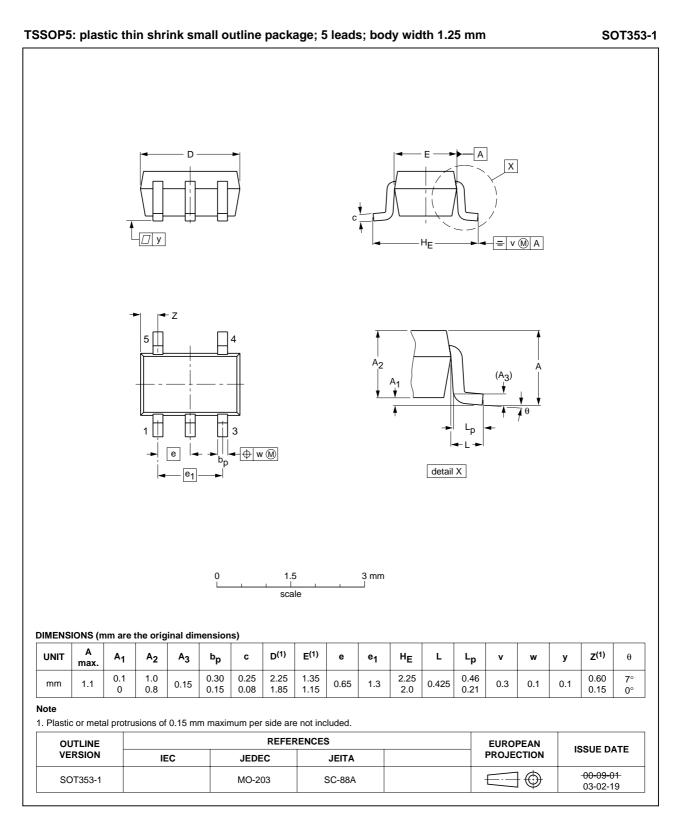


For 74HCT1G14: 
$$f = \frac{l}{T} \approx \frac{l}{0.67 \times RC}$$

Fig 16. Relaxation oscillator using 74HC1G14 and 74HCT1G14

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## 16. Package outline



### Fig 17. Package outline SOT353-1 (TSSOP5)

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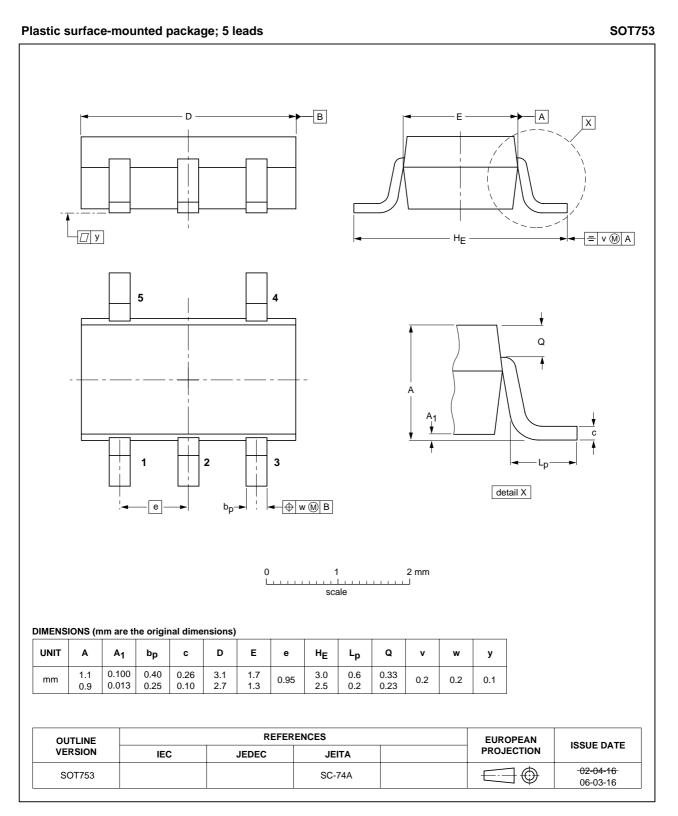


Fig 18. Package outline SOT753 (SC-74A)

# **17. Abbreviations**

Table 10. Abbreviations					
Acronym	Description				
DUT	Device Under Test				
TTL	Transistor-Transistor Logic				

# **18. Revision history**

### Table 11.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
74HC_HCT1G14_4	20070717	Product data sheet	-	74HC_HCT1G14_3			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>						
	<ul> <li>Legal texts</li> </ul>	s have been adapted to the r	new company name whe	ere appropriate.			
	<ul> <li>Package S</li> </ul>	OT353 changed to SOT353	-1 in <u>Table 1</u> and <u>Figure</u>	<u>17</u> .			
	<ul> <li>Quick Refe</li> </ul>	erence Data and Soldering s	ections removed.				
	Section 2 <sup>c</sup>	'Features" updated.					
74HC_HCT1G14_3	20020515	Product specification	-	74HC_HCT1G14_2			
74HC_HCT1G14_2	20010302	Product specification	-	74HC_HCT1G14_1			
74HC_HCT1G14_1	19980805	Product specification	-	-			

# **19. Legal information**

## **19.1 Data sheet status**

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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